--(5) A reflection prevention film 99 may be formed on the third wiring layer 40. It is noted that, when a reflection prevention film 99 is formed, the reflection prevention film 99 at the pad opening section 60 may preferably be removed in order to improve the coherency between bonding structures (for example, bonding balls, bumps, etc.) and the third wiring layer 40. The reflection prevention film 99 may be formed from, for example, a titanium nitride film. The thickness of such a titanium nitride film is, for example, 20 – 80 nm.--

IN THE CLAIMS:

Please cancel claims 21 and 23 without prejudice.

Please amend claims 1, 5, 8, 17, 20 and 22 as follows:

1. (amended) A semiconductor device comprising:

a protective insulation layer;

a pad opening section provided in the protective insulation layer;

a wiring layer which the pad opening section reaches;

a reflection prevention film on at least a portion of the wiring layer that the pad opening section reaches; and

a wiring layer provided at a level lower than the wiring layer which the pad opening section reaches,

wherein the wiring layer provided at a level lower than the wiring layer which the pad opening section reaches is formed outside a region of the pad opening section as viewed in a plan view.

5. (amended) A semiconductor device comprising:

a first wiring layer formed above a semiconductor layer and above a first interlayer insulation layer;

a second wiring layer that includes a pad section formed above the first wiring layer and above a second interlayer insulation layer;

a reflection prevention film on at least a portion of the second wiring layer;

a protective insulation layer formed above the second wiring layer and the second interlayer insulation layer; and

a pad opening section provided in the protective insulation layer,

wherein an upper surface of the first interlayer insulation layer includes a first region where the protective insulation layer is formed vertically thereabove, and

the first wiring layer is formed on the first region.

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8. (amended) A method for manufacturing a semiconductor device, the method comprising the steps of:

(a) forming a wiring layer on an interlayer insulation layer and a reflection prevention film on the wiring layer;

(b) forming a protective insulation layer on the interlayer insulation layer and over the wiring layer and the reflection prevention film; and

(c) forming a pad opening section in the protective insulation layer and the reflection prevention film, which reaches the wiring layer,

wherein the semiconductor device includes a wiring layer provided at a level lower than the wiring layer to which the pad opening section reaches,

wherein the pad opening section is formed such that the wiring layer provided at a level lower than the wiring layer to which the pad opening section reaches is formed outside a region of the pad opening section as viewed in a plan view.

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17. (amended) A method for manufacturing a semiconductor device, comprising:

forming a lower level wiring layer;

forming a lower level interlayer dielectric layer on and adjacent to the lower level wiring layer;

forming an upper level wiring layer above the lower level interlayer dielectric layer, wherein the lower level wiring layer is electrically connected to the upper level wiring layer;

forming a reflection prevention film on the upper level wiring layer;

forming a protective insulation layer on the upper level wiring layer;

removing a first portion of the protective insulation layer over the upper level wiring layer and over the lower level interlayer dielectric layer to form a pad opening section;

wherein a second portion of the protective insulation layer located vertically above the lower level wiring layer remains after removing the first portion of the protective layer; and

wherein no portion of the lower level wiring layer is disposed vertically below the pad opening section.

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20. (amended) A method as in claim 18, further comprising:

forming the lower level wiring layer to be electrically connected to the intermediate level wiring layer;

forming the intermediate level wiring layer to be electrically connected to the upper level wiring layer;

forming the lower level wiring layer to include a thickness that is less than that of the lower level interlayer dielectric layer;

forming the intermediate level wiring layer to include a thickness that is less than that of the intermediate level interlayer dielectric layer;

forming a plurality of lower level plugs to electrically connect the lower level wiring layer to the intermediate level wiring layer;

forming a plurality of intermediate level plugs to electrically connect the intermediate level wiring layer to the upper level wiring layer; and

wherein the intermediate plugs are formed to be offset from the lower level intermediate plugs in a vertical direction.

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22. (amended) A method as in claim 17, further comprising removing the reflection prevention film from the pad opening section of the upper level wiring layer.

Please add new claims 24-25 as follows:

A8

--24. (new) A semiconductor device according to claim 1, wherein the wiring layer that the pad opening section reaches includes a first portion along the pad opening section and a second portion adjacent to the pad opening section, and wherein the reflection prevention film is located only on the second portion.

B

25. (new) A semiconductor device according to claim 5, wherein the second wiring layer includes a region positioned adjacent to the pad section, and wherein the reflection prevention film is located only on the region positioned adjacent to the pad section.--